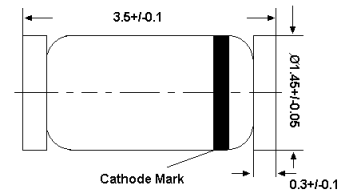


# RLS245

## Silicon Epitaxial Planar Diode

High Voltage Switching Diode

LL-34



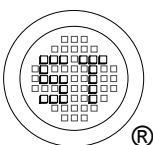
Glass case MiniMELF  
Dimensions in mm

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	$V_{RM}$	250	V
Reverse Voltage	$V_R$	220	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Maximum Forward Current	$I_{FM}$	625	mA
Surge Forward Current at $t < 1\text{ s}$ and $T_j = 25\text{ }^\circ\text{C}$	$I_{FSM}$	1000	mA
Junction Temperature	$T_j$	175	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 65 to + 175	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 200\text{ mA}$	$V_F$	-	1.5	V
Leakage Current at $V_R = 220\text{ V}$	$I_R$	-	10	$\mu\text{A}$
Reverse Breakdown Voltage at $I_R = 100\text{ }\mu\text{A}$	$V_{BR}$	250	-	V
Capacitance at $V_F = V_R = 0, f = 1\text{ MHz}$	$C_{tot}$	-	3	pF
Reverse Recovery Time from $I_F = I_R = 20\text{ mA}$	$t_{rr}$	-	75	ns



**SEMTECH ELECTRONICS LTD.**  
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